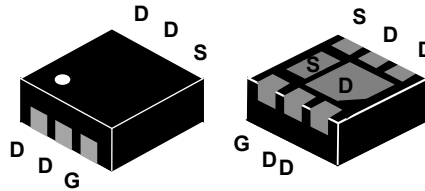
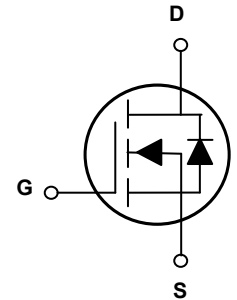


### Main Product Characteristics

$V_{(BR)DSS}$	30V
$R_{DS(ON)}$	13m $\Omega$
$I_D$	10A



DFN2x2-6L 2EP



Schematic Diagram

### Features and Benefits

- Advanced MOSFET process technology
- Ideal for battery operated systems, load switching, power converters and other general purpose applications
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



### Description

The SSFB3910L utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

### Absolute Maximum Ratings (T<sub>C</sub>=25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	±20	V
Drain Current – Continuous (T <sub>A</sub> =25°C)	$I_D$	10	A
Drain Current – Continuous (T <sub>A</sub> =70°C)		8	A
Drain Current – Pulsed <sup>1</sup>	$I_{DM}$	40	A
Single Pulse Avalanche Energy <sup>2</sup>	$E_{AS}$	13	mJ
Single Pulse Avalanche Current <sup>2</sup>	$I_{AS}$	16	A
Power Dissipation (T <sub>C</sub> =25°C)	$P_D$	2.01	W
Power Dissipation – Derate above 25°C		0.016	W/°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C
Operating Junction Temperature Range	T <sub>J</sub>	-55 to +150	°C

### Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	---	62	°C/W

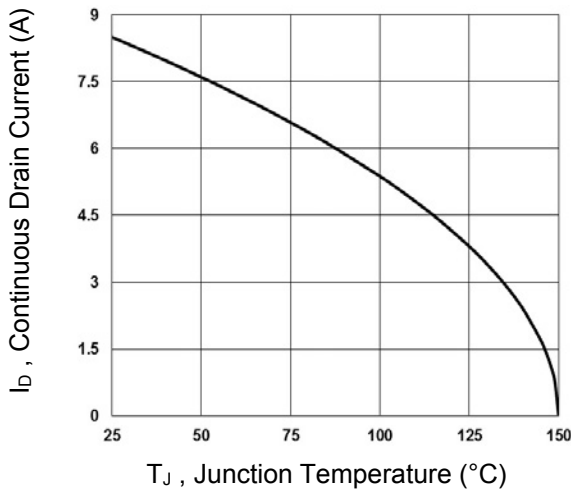
### Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	---	---	V
BV <sub>DSS</sub> Temperature Coefficient	ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Reference to 25°C, I <sub>D</sub> =1mA	---	0.04	---	V/°C
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	10	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
<b>On Characteristics</b>						
Static Drain-Source On-Resistance <sup>3</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =6A	---	10.2	13	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A	---	13.3	18	mΩ
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.8	2.5	V
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub>		---	-4	---	mV/°C
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =3A	---	6	---	S
<b>Dynamic and Switching Characteristics</b>						
Total Gate Charge <sup>3, 4</sup>	Q <sub>g</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	---	7.4	12	nC
Gate-Source Charge <sup>3, 4</sup>	Q <sub>gs</sub>		---	2.3	5	
Gate-Drain Charge <sup>3, 4</sup>	Q <sub>gd</sub>		---	3	6	
Turn-On Delay Time <sup>3, 4</sup>	T <sub>d(on)</sub>	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω I <sub>D</sub> =1A	---	3.8	7	nS
Rise Time <sup>3, 4</sup>	T <sub>r</sub>		---	10	19	
Turn-Off Delay Time <sup>3, 4</sup>	T <sub>d(off)</sub>		---	22	42	
Fall Time <sup>3, 4</sup>	T <sub>f</sub>		---	6.6	13	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, F=1MHz	---	620	900	pF
Output Capacitance	C <sub>oss</sub>		---	85	125	
Reverse Transfer Capacitance	C <sub>rss</sub>		---	60	90	
Gate Resistance	R <sub>g</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	---	2.8	5.6	Ω
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Continuous Source Current	I <sub>S</sub>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	10	A
Pulsed Source Current <sup>3</sup>	I <sub>SM</sub>		---	---	20	A
Diode Forward Voltage <sup>3</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V

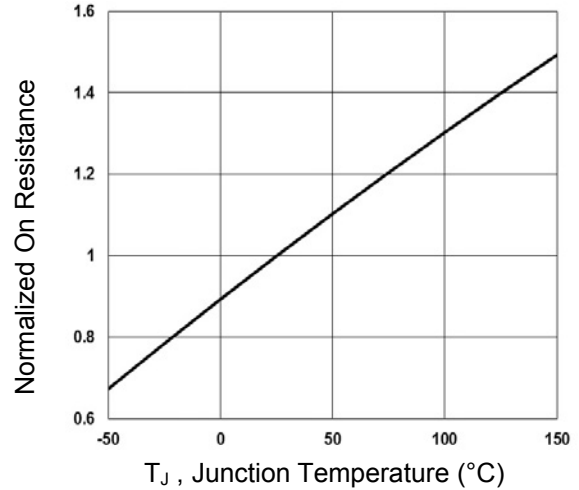
**Notes:**

1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
2. V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=16A, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C.
3. The data tested by pulsed, pulse width ≤ 300uS, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

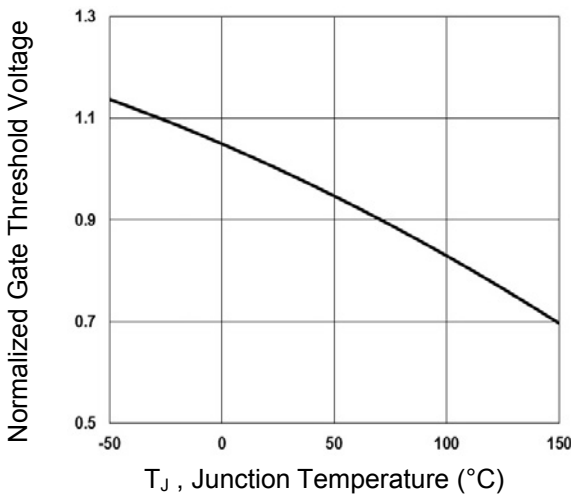
### Typical Electrical and Thermal Characteristic Curves



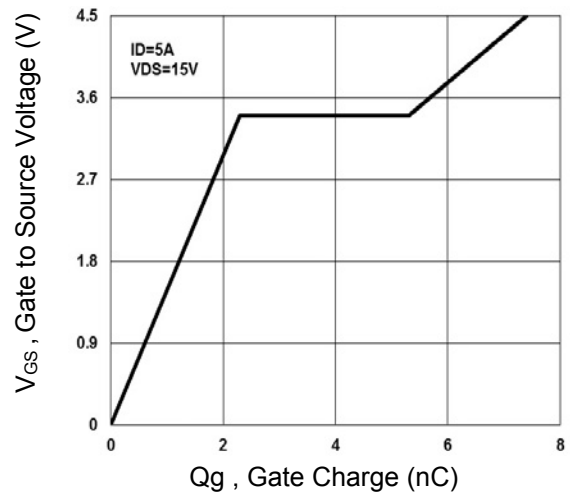
**Fig.1 Continuous Drain Current vs.  $T_c$**



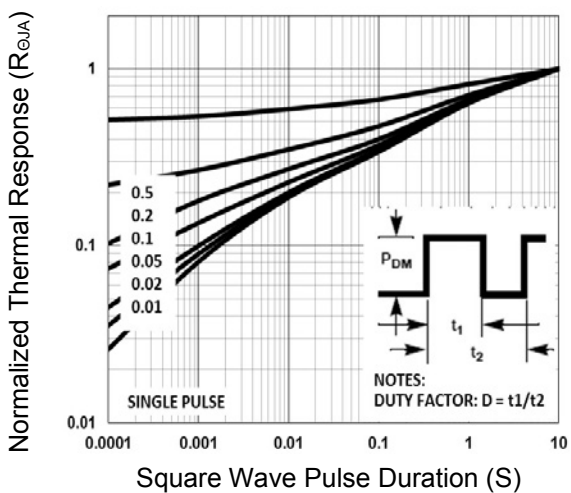
**Fig.2 Normalized  $R_{DS(ON)}$  vs.  $T_J$**



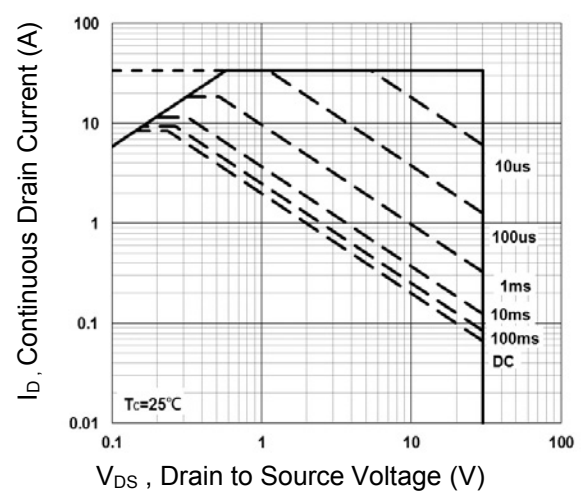
**Fig.3 Normalized  $V_{th}$  vs.  $T_J$**



**Fig.4 Gate Charge Waveform**

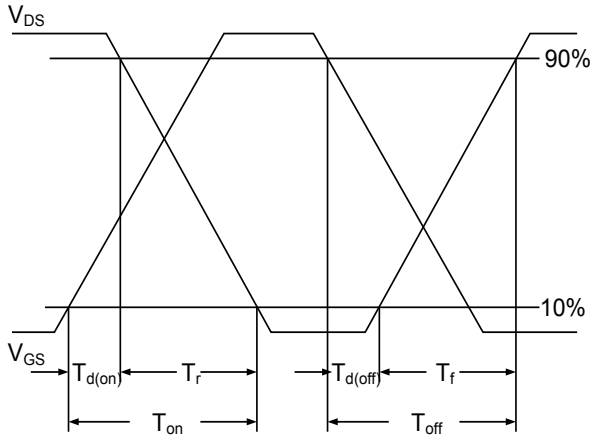


**Fig.5 Normalized Transient Response**

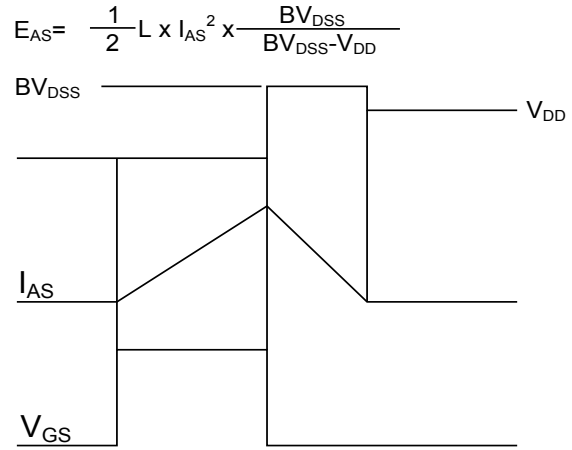


**Fig.6 Maximum Safe Operation Area**

## Typical Electrical and Thermal Characteristic Curves



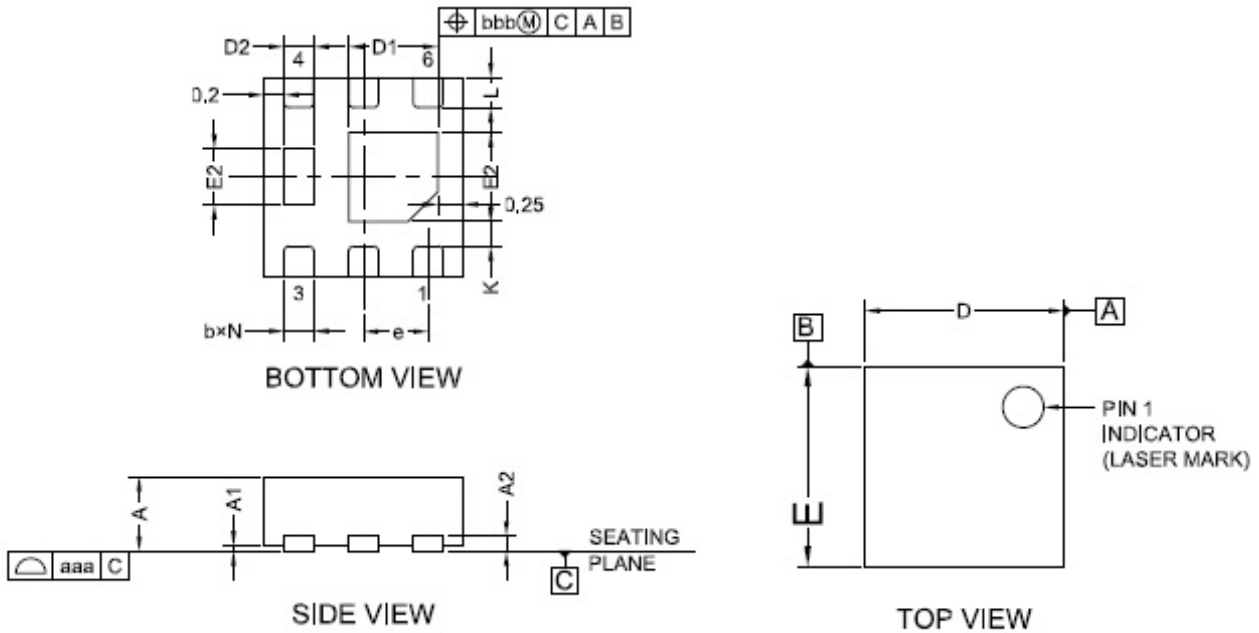
**Fig.7 Switching Time Waveform**



**Fig.8  $E_{AS}$  Waveform**

## Package Outline Dimensions

## DFN2x2-6L 2EP



Symbol	Dimensions In Millimeters		
	Min	Typ	Max
A	0.50	0.55	0.60
A1	0.00	0.02	0.05
A2	0.152REF		
b	0.25	0.30	0.35
D	1.95	2.00	2.05
D1	0.80	0.90	1.00
D2	0.25	0.30	0.35
E	1.95	2.00	2.05
E1	0.80	0.90	1.00
E2	0.46	0.56	0.66
e	0.65BSC		
L	0.25	0.30	0.35
J	0.40BSC		
K	0.20MIN		
N	6.00		
aaa	0.08		
bbb	0.10		